

## N-Channel Enhancement Mode Power MOSFET

### Features:

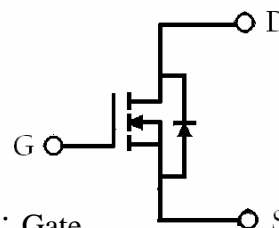
- Simple Drive Requirement
- Repetitive Avalanche Rated
- Fast Switching Characteristic
- RoHS compliant package
- Pb-free lead plating and halogen-free package

TO-252(DPAK)



G D S

BV <sub>DSS</sub>		100V
I <sub>D</sub>		50A
R <sub>DS(on)(TYP)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	17mΩ
	V <sub>GS</sub> =5V, I <sub>D</sub> =20A	19mΩ



G : Gate  
D : Drain  
S : Source

### Ordering Information

Device	Package	Shipping
KJD20N10	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel

**Absolute Maximum Ratings** ( $T_C=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	$V_{DS}$	100	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current @ $T_C=25^{\circ}\text{C}$ , $V_{GS}=10\text{V}$	$I_D$	50	A	
Continuous Drain Current @ $T_C=100^{\circ}\text{C}$ , $V_{GS}=10\text{V}$	$I_D$	35		
Pulsed Drain Current (Note 1)	$I_{DM}$	150		
Avalanche Current	$I_{AS}$	30		
Avalanche Energy @ $L=0.1\text{mH}$ , $I_D=30\text{A}$ , $R_G=25\ \Omega$	$E_{AS}$	45	mJ	
Repetitive Avalanche Energy @ $L=0.05\text{mH}$ (Note 2)	$E_{AR}$	22.5		
Power Dissipation	$T_C=25^{\circ}\text{C}$	$P_D$	60	W
	$T_C=100^{\circ}\text{C}$		32	
Operating Junction and Storage Temperature	$T_j, T_{stg}$	-55~+175	$^{\circ}\text{C}$	

Note : 1. Pulse width limited by maximum junction temperature  
 2. Duty cycle  $\leq 1\%$

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	2.5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	50 (Note)	$^{\circ}\text{C}/\text{W}$

Note : When the device is mounted on 1 in<sup>2</sup> FR-4 board with 2 oz. copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design.

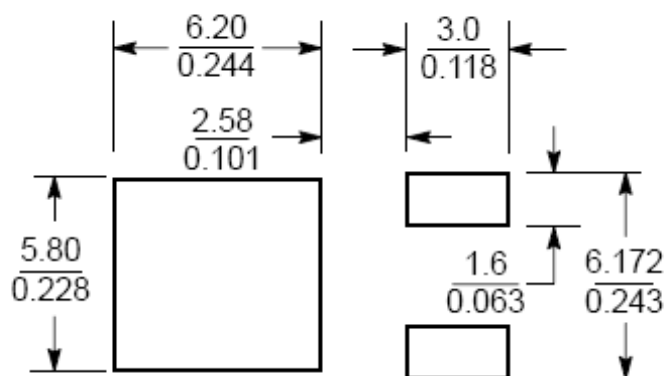
**Characteristics** ( $T_C=25^{\circ}\text{C}$ , unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
$BV_{DSS}$	100	-	-	V	$V_{GS}=0\text{V}$ , $I_D=250\ \mu\text{A}$
$V_{GS(th)}$	1.0	2.4	3.0		$V_{DS} = V_{GS}$ , $I_D=250\ \mu\text{A}$
$G_{FS}$	-	38	-	S	$V_{DS} = 5\text{V}$ , $I_D=30\text{A}$
$I_{GSS}$	-	-	$\pm 100$	nA	$V_{GS}=\pm 20$
$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS} = 80\text{V}$ , $V_{GS} = 0\text{V}$
	-	-	25		$V_{DS} = 70\text{V}$ , $V_{GS} = 0\text{V}$ , $T_j=125^{\circ}\text{C}$
* $R_{DS(ON)}$	-	17	25	$\text{m}\Omega$	$V_{GS} = 10\text{V}$ , $I_D=30\text{A}$
	-	19	30		$V_{GS} = 5\text{V}$ , $I_D=20\text{A}$
<b>Dynamic</b>					
* $Q_g$	-	25	-	nC	$V_{DS}=50\text{V}$ , $I_D=30\text{A}$ , $V_{GS}=10\text{V}$
* $Q_{gs}$	-	6.1	-		
* $Q_{gd}$	-	9.2	-		
* $t_{d(ON)}$	-	19	-	ns	$V_{DS}=50\text{V}$ , $I_D=1\text{A}$ , $V_{GS}=10\text{V}$ , $R_G=6\ \Omega$
* $t_r$	-	67	-		
* $t_{d(OFF)}$	-	75	-		
* $t_f$	-	34	-		

Ciss	-	1888	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz
Coss	-	236	-		
Crss	-	124	-		
Rg	-	2	-	Ω	V <sub>GS</sub> =15mV, V <sub>DS</sub> =0V, f=1MHz
<b>Source-Drain Diode</b>					
*I <sub>S</sub>	-	-	50	A	
*I <sub>SM</sub>	-	-	150		
*V <sub>SD</sub>	-	0.88	1.3	V	I <sub>F</sub> =I <sub>S</sub> , V <sub>GS</sub> =0V
*trr	-	120	-	ns	I <sub>F</sub> =25A, V <sub>GS</sub> =0, dI/dt=100A/μs
*Qrr	-	380	-	nC	

\*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

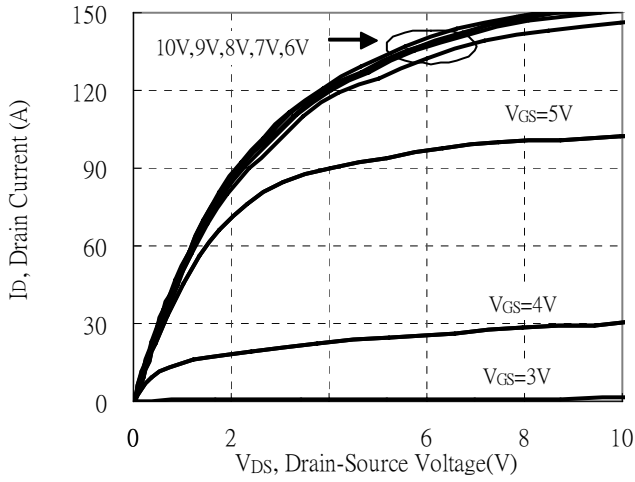
**Recommended soldering footprint**



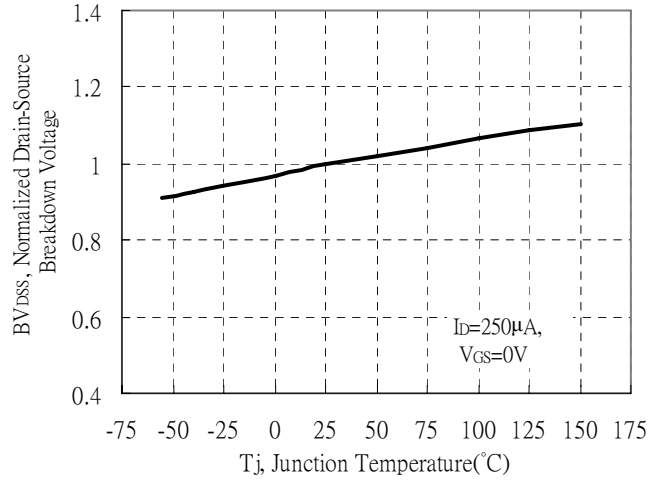
Unit (  $\frac{\text{mm}}{\text{inch}}$  )

**Typical Characteristics**

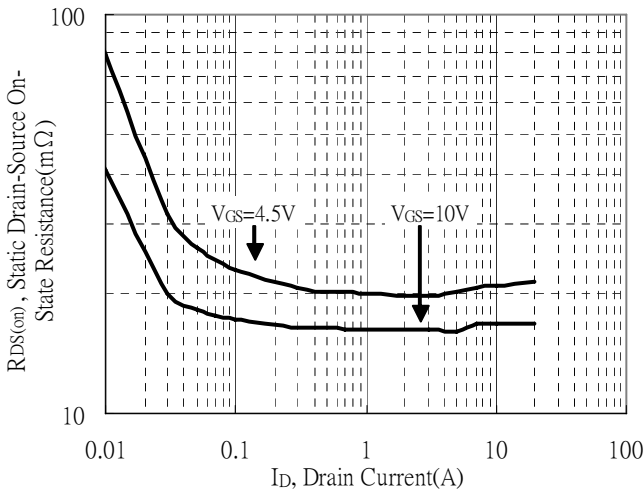
Typical Output Characteristics



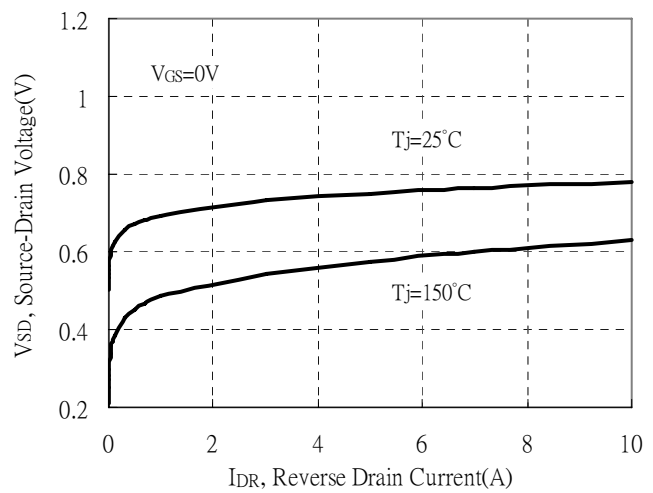
Brekdown Voltage vs Ambient Temperature



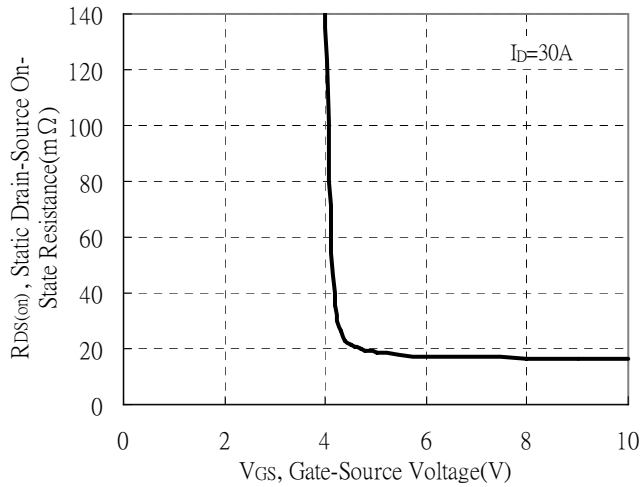
Static Drain-Source On-State resistance vs Drain Current



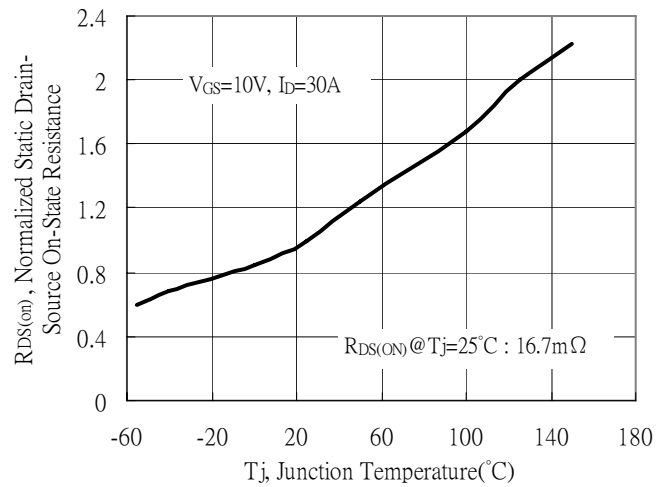
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

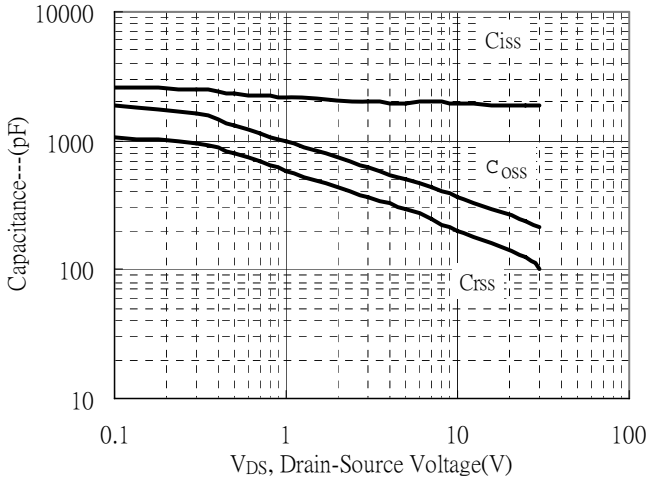


Drain-Source On-State Resistance vs Junction Temperature

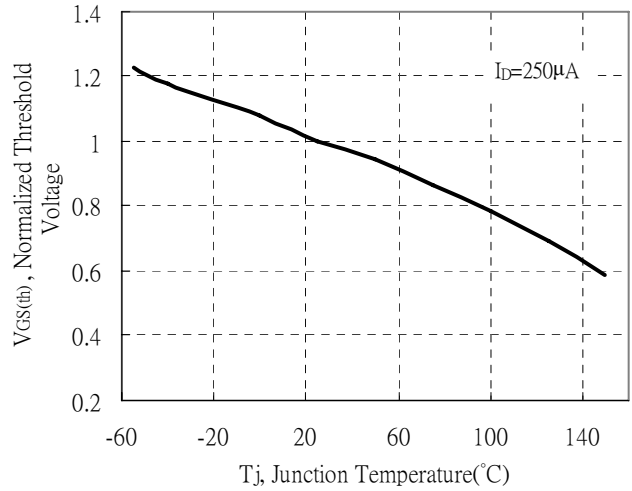


**Typical Characteristics (Cont.)**

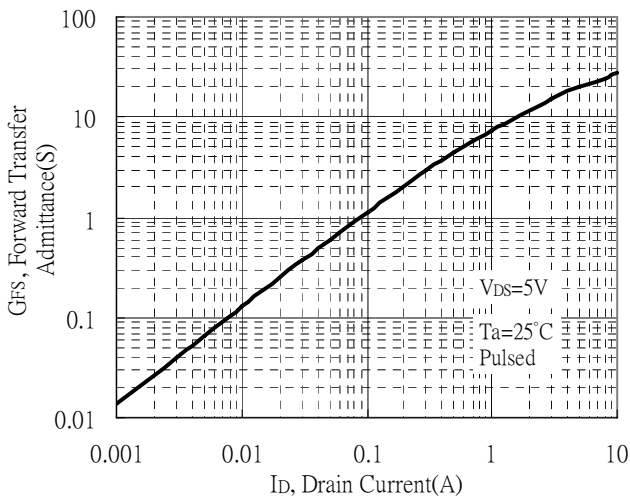
Capacitance vs Drain-to-Source Voltage



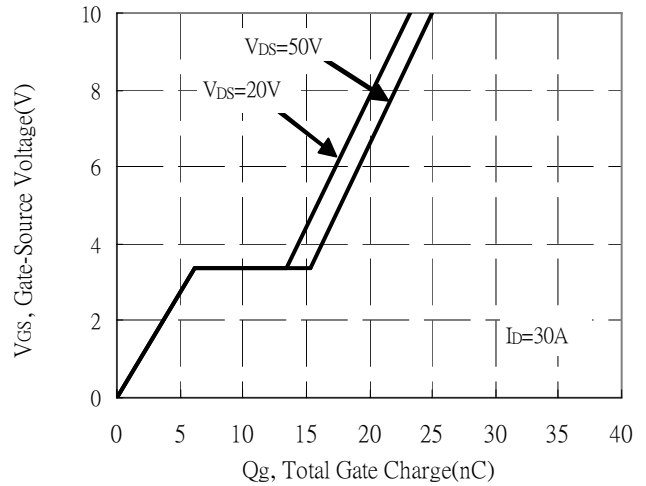
Threshold Voltage vs Junction Temperature



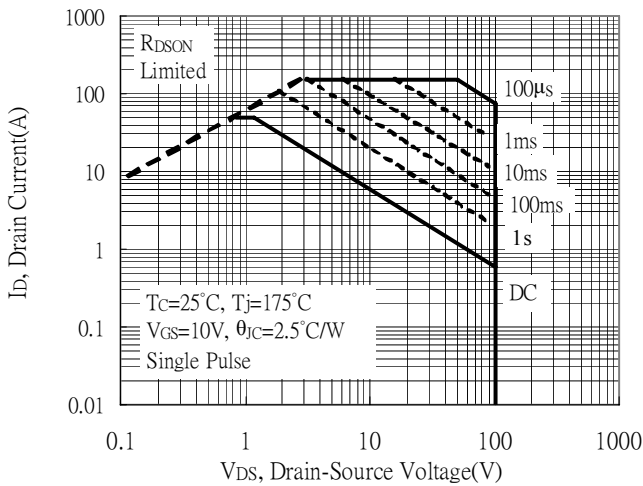
Forward Transfer Admittance vs Drain Current



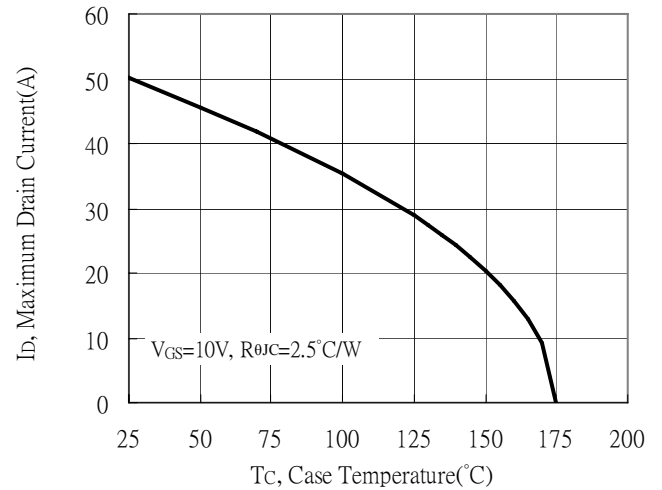
Gate Charge Characteristics



Maximum Safe Operating Area

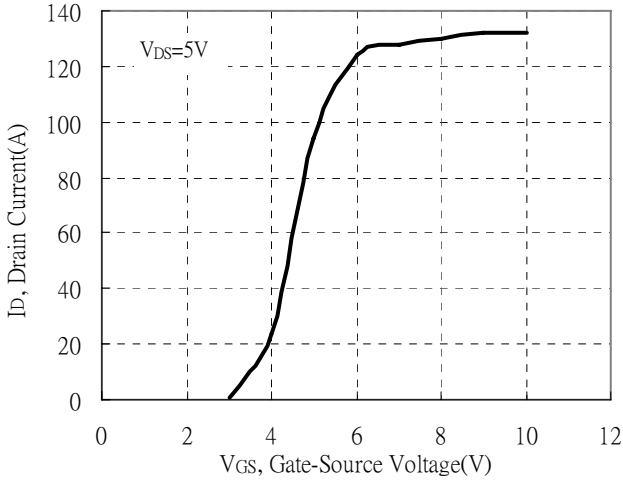


Maximum Drain Current vs Case Temperature

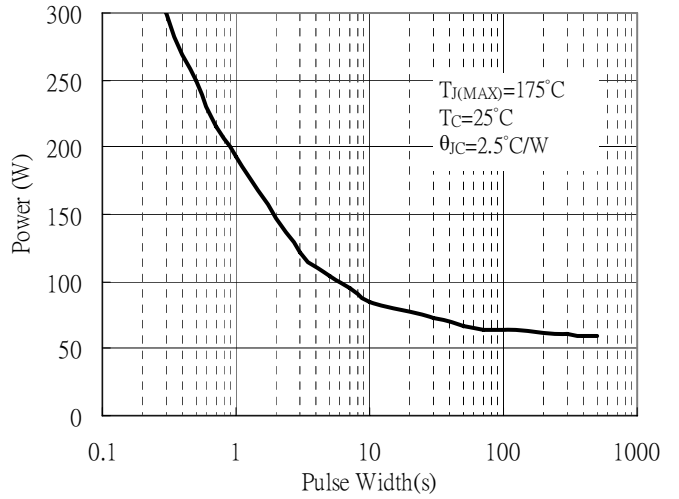


**Typical Characteristics (Cont.)**

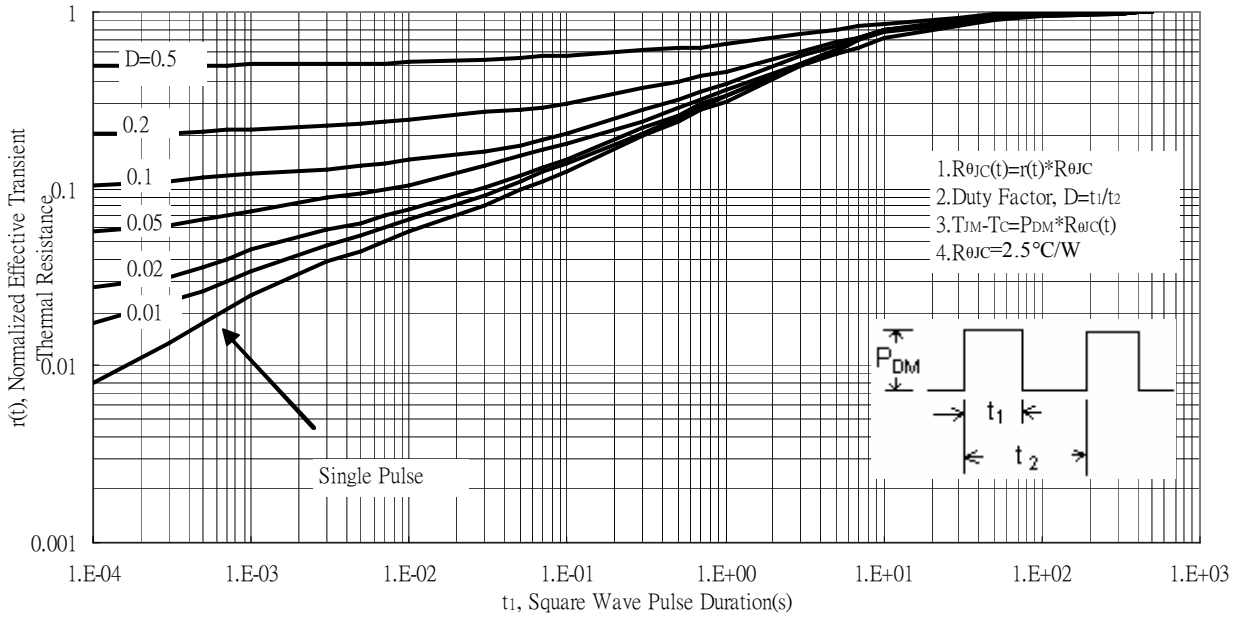
Typical Transfer Characteristics



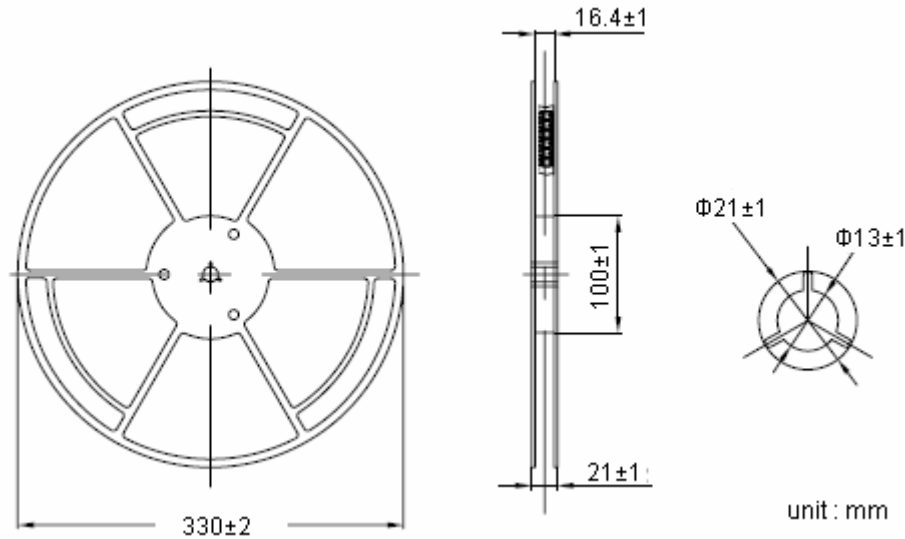
Single Pulse Power Rating, Junction to Case



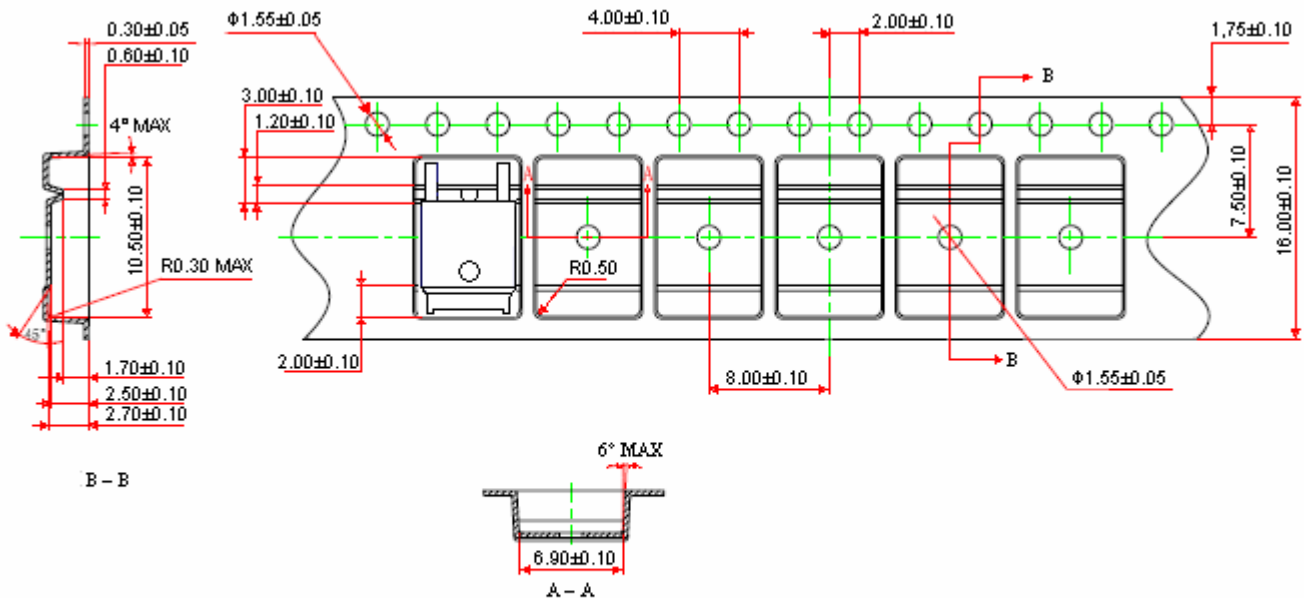
Transient Thermal Response Curves



### Reel Dimension



### Carrier Tape Dimension

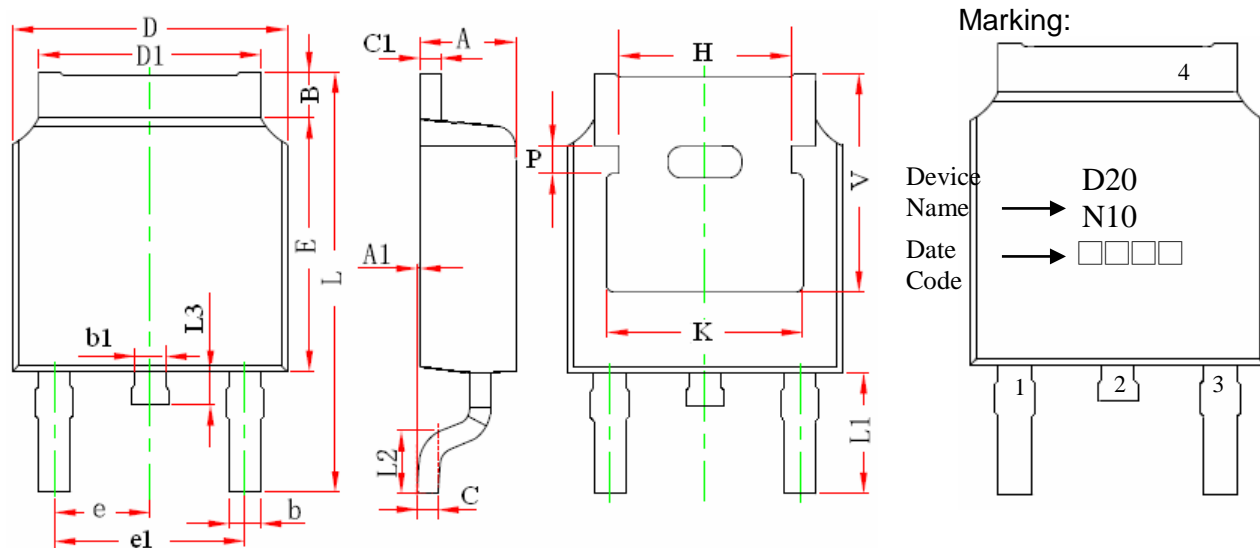


**Notes:**

1. 10 sprocket hole pitch cumulative tolerance  $\pm 0.2$ .
2. Camber not to exceed 1mm in 100mm.
3. Material: conductive black polystyrene, antistatic coated :  $10^5 \Omega/\square \sim 10^{11} \Omega/\square$

unit : mm

**TO-252 Dimension**



3-Lead TO-252 Plastic Surface Mount Package

Style: Pin 1.Gate 2.Drain 3.Source 4.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF